

a second metallic layer formed on said first metallic layer;
a second insulating film formed on said second metallic layer;
and

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a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer through a contact hole provided in said second insulating film, wherein said conductive layer and said second metallic layer are connected to each other at the bottom of a contact hole provided in said first insulating film.

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7. (Amended) A semiconductor device comprising:

a first insulating film comprising an organic material formed over a thin film transistor;

a first metallic layer formed on said first insulating film;
a second metallic layer formed on said first metallic layer;
a second insulating film formed on said second metallic layer;

and
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a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer through a contact hole provided in said second insulating film,

wherein a source region or a drain region of said thin film transistor and said second metallic layer are connected to each other at the bottom of a contact hole provided in said first insulating film.

19. (Amended) A semiconductor device comprising:

B3 a first insulating film comprising an organic material formed over a thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

pub D3 a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein a source region or a drain region and said second conductive layer are connected to each other at the bottom of a contact hole provided in said first insulating film,

wherein said second conductive layer is contact with said first insulating film inside of said contact holes.

28. (Amended) A semiconductor device comprising:

B4 pub D4 a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed there between;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;
a second conductive layer formed on said first conductive layer;

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a second insulating film formed on said second conductive layer; and

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a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein said second conductive layer is connected to said semiconductor layer through a contact hole provided in said first insulating film.

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34. (Amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

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a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;
a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

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wired

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein said second conductive layer is connected to said semiconductor layer through a contact hole provided in said first conductive layer and said first insulating film.

PLEASE ADD THE FOLLOWING NEW CLAIMS 40-45.

40. A semiconductor device comprising:

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a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed there between;

a first insulating film formed over said thin film transistor;

a first wiring formed on said first insulating film;

a second wiring formed on said first wiring;

a second insulating film formed on said second wiring; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second wiring through a contact hole provided in said second insulating film,

wherein said second wiring is connected to said semiconductor layer through a contact hole provided in said first insulating film.

41. The semiconductor device according to claim 40, wherein said first conductive layer is selected from the group consisting of aluminum and a material predominantly composed of aluminum.

42. The semiconductor device according to claim 40, wherein said second conductive layer is selected from the group consisting of titanium and a material predominantly composed of titanium.

43. The semiconductor device according to claim 40, wherein said organic material is an organic-based resin material predominantly selected from the group consisting of polyimide, polyimide-amide, polyamide, acrylics, and BCB (benzocyclobutane).

44. The semiconductor device according to claim 40, wherein said semiconductor device is selected from the group consisting of an active matrix liquid-crystal display device, an active matrix EL display device, and an active matrix EC display device.

45. The semiconductor device according to claim 40, wherein said semiconductor device is selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display device, a car navigation device, a personal computer, and a portable information terminal.
